Contents

1 General Features and Fundamental Concepts 1
1.1 Introduction 1
1.2 Range Distributions 2
1.3 Lattice Disorder 3
1.4 Atomic and Planar Densities 5
1.5 Energy and Particles 6
1.6 The Bohr Velocity and Radius 8
Suggested Reading 9
Problems 9

2 Particle Interactions 11
2.1 Introduction 11
2.2 Interatomic Forces 11
2.3 Short- and Long-Range Interatomic Forces 12
2.4 Interatomic Forces in Solids 13
2.5 Energetic Collisions of Atoms and Ions and the Screened Coulomb Potential 15
2.6 Screening Functions 16
2.7 Screening Length 18
References 20
Suggested Reading 20
Problems 21

3 Dynamics of Binary Elastic Collisions 23
3.1 Introduction 23
3.2 Classical Scattering Theory 24
3.3 Kinematics of Elastic Collisions 25
3.4 Center-of-Mass Coordinates 27
3.5 Motion Under a Central Force 30
3.5.1 Energy Conservation in a Central Force 31
3.5.2 Angular Orbital Momentum and the Impact Parameters 32
3.6 Distance of Closest Approach 34
References 35
Suggested Reading 35
Problems 35

4 Cross-Section 37
4.1 Introduction 37
4.2 Scattering Cross-Section 37
4.3 Energy-Transfer Cross-Section 42
4.4 Approximation to the Energy-Transfer Cross-Section 45
References 47
Suggested Reading 47
Problems 47

5 Ion Stopping 49
5.1 Introduction 49
5.2 The Energy-Loss Process 50
5.3 Nuclear Stopping 51
5.4 ZBL Nuclear Stopping Cross-Section 54
5.5 Electronic Stopping 56
5.5.1 High-Energy Electronic Energy Loss 57
5.5.2 Low-Energy Electronic Energy Loss 58
5.6 Stopping Calculations Using SRIM 60
References 60
Suggested Reading 60
Problems 61

6 Ion Range and Range Distribution 63
6.1 Range Concepts 63
6.2 Range Distributions 65
6.3 Calculations 67
6.3.1 Range Approximations 67
6.3.2 Projected Range 68
6.3.3 Range Straggling 70
6.3.4 Polyatomic Targets 71
6.4 Range Distributions from SRIM 72
References 74
Suggested Reading 75
Problems 75

7 Displacements and Radiation Damage 77
7.1 Introduction 77
7.2 Radiation Damage and Displacement Energy 77
7.3 Displacements Produced by a Primary Knock-on 79
7.4 Primary Knock-on Atom Damage Energy 82
7.5 Ion Damage Energy 83
7.6 Damage Production Rate and DPA 85
7.7 Replacement Collision Sequences 86
7.8 Spikes 86
7.8.1 Mean Free Path and the Displacement Spike 86
7.8.2 Thermal Spike 87

7.9 Damage Distribution from SRIM ... 89
References ... 91
Suggested Reading ... 91
Problems ... 91

8 Channeling ... 93
8.1 Introduction ... 93
8.2 General Principles ... 96
8.3 The Maximum Range, R_{max} ... 99
8.4 Dechanneling by Defects ... 100
References ... 105
Problems ... 106

9 Doping, Diffusion and Defects in Ion-Implanted Si ... 107
9.1 Junctions and Transistors ... 107
9.1.1 Bipolar Transistors ... 109
9.1.2 Metal-Oxide-Semiconductor Field-Effect Transistors ... 110
9.1.3 Complementary Metal Oxide Semiconductor Devices ... 112
9.2 Defects ... 114
9.2.1 Point Defects ... 114
9.2.2 Native Defects and Shallow Dopants ... 114
9.2.3 Deep Level Centers ... 115
9.2.4 Line Defects ... 116
9.2.5 Planar Defects ... 117
9.2.6 Volume Defects ... 117
9.3 Fick's First and Second Law of Diffusion ... 118
9.3.1 Diffusion Coefficient ... 119
9.3.2 Diffusion of Doping Atoms into Si ... 119
9.4 Diffusion Mechanisms ... 119
9.4.1 Interstitial Mechanism ... 121
9.4.2 Substitutional or Vacancy Mechanism ... 121
9.4.3 Interstitial–Substitutional Mechanism ... 121
9.4.4 Interstitialcy and the Kick-Out Mechanism ... 122
9.5 Transient Enhanced Diffusion of Boron ... 122
9.6 Irradiation–Enhanced Diffusion ... 124
References ... 125
Problems ... 126

10 Crystallization and Regrowth of Amorphous Si ... 127
10.1 Introduction ... 127
10.2 Epitaxial Growth of Implanted Amorphous Si ... 129
10.3 Ion Beam-Induced Enhanced Crystallization ... 137
10.4 Laser Annealing of Si ... 140
References ... 141
Problems ... 142

11 Si Slicing and Layer Transfer: Ion-Cut 143
11.1 Introduction 143
11.2 Formation of SOI by the Ion-Cut Process 144
11.3 The Silicon–Hydrogen System 145
11.4 The Mechanisms Behind the Ion-Cut Process 149
11.4.1 The Ion-Cut Depth 149
11.4.2 Microstructure of the Implantation Zone 153
References 157

12 Surface Erosion During Implantation: Sputtering 159
12.1 Introduction 159
12.2 Sputtering of Single-Element Targets 159
12.3 Ion Implantation and the Steady State Concentration 162
12.4 Sputtering of Alloys and Compounds 164
12.4.1 Preferential Sputtering 165
12.4.2 Compositional Changes 166
12.4.3 Composition Depth Profiles 168
12.5 High-Dose Ion Implantation 169
12.6 Concentrations of Implanted Species 171
12.6.1 Si Implanted with 45 keV Pt Ions 171
12.6.2 Pt Implanted with 45 keV Si Ions 172
12.6.3 PtSi Implanted with Si 172
12.7 Concentrations in High-Dose Ion Implantation 173
12.8 Computer Simulation 175
References 176
Suggested Reading 176
Problems 177

13 Ion-Induced Atomic Intermixing at the Interface: Ion Beam Mixing 179
13.1 Introduction 179
13.2 Ballistic Mixing 182
13.2.1 Recoil Mixing 183
13.2.2 Cascade Mixing 185
13.3 Thermodynamic Effects in Ion Mixing 187
References 191
Suggested Reading 191
Problems 192

14 Application of Ion Implantation Techniques in CMOS Fabrication 193
14.1 Introduction 193
14.2 Issues During Device Scaling 193
14.2.1 Short-Channel Effects 195
14.2.2 Hot-Electron Effect 197
14.2.3 Latchup 198
14.3 Ion Implantation in Advanced CMOS Device Fabrication 199
14.3.1 Retrograde Well Implant 202

14.3.2 Punch-Through Stop Implant 203
14.3.3 Threshold Adjust Implant 203
14.3.4 Source and Drain Implant 205
14.3.5 Halo Implant 206
14.3.6 Gate Implant 207
14.4 Issues of Ion Implantation During Device Scaling 207
14.4.1 Space Charge Effects 207
14.4.2 Energy Contamination 208
14.4.3 Beam Shadowing Effect 208
14.5 The Role of Ion Implantations in Device Fabrications 208
References 209
Suggested Reading 210
Problems 210

15 Ion implantation in CMOS Technology: Machine Challenges 213
15.1 Introduction 213
15.2 Implanters used in CMOS Processing 214
15.2.1 Beamline Architectures 215
15.2.2 Other Subsystems 221
15.3 Low Energy Productivity: Beam Transport 223
15.3.1 Space Charge Neutralization 224
15.3.2 Decel Implantation 224
15.3.3 Molecular Implantation 226
15.4 Low Energy Productivity: Beam Utilization 226
15.4.1 Beam Utilization 227
15.4.2 Implanters Commercialized in the Past 35 Years 230
15.5 Angle Control 232
15.5.1 Impact of Beam Steering Errors on Device Performance 232
15.5.2 Impact of Endstation Design and Beam Scan Mechanism 234
15.6 Conclusions and the Future of Ion Implantation in Semiconductors 236
References 237

Appendix A: Table of the Elements 239
Appendix B: Physical Constants, Conversions, and Useful Combinations 255

Index 257